CIR-W4DUSW2616G

DDR4 WIDE TEMP. DIMM 2666MHz 16GB

Description

CIR-W4DUSW2616G is a CMOS Double Data Rate IV (DDR4) Synchronous DRAM module, in Fine Ball Grid Array(FBGA) packages on a 288pin glass-epoxy substrate.

DDR4 unbuffered UDIMM series offers fully synchronous operations referenced to both rising and falling edges of the clock. The data paths are internally pipelined and 8-bit prefetched to achieve very high bandwidth.

Specifications

Density	16GB
Pin Count	288pin
Type	Unbuffered
Dimensions	133.35mm x 31.25mm
ECC	Non-ECC
Component Config	1G x 8 bit
Data Rate	2666 MHz
CAS Latency	19
Voltage	1.2V
PCB Layers	8
Operating Temp.(TCASE)	-40°C~+95°C
Module Ranks	Dual Rank

Features

- JEDEC standard
- VDD=VDDQ = 1.2V±0.06V (1.14V~1.26V)
- Programmable CAS Latency(posted CAS): 11,12,13,14,15,16,17,18,19
- 8-bit pre-fetch
- 16 Banks (4 Bank Groups)
- Internal(self) calibration : Internal self calibration through ZQ pin
- On Die Termination using ODT pin
- Average Refresh Period
  - 7.8us (TCASE ≤ 85˚C)
  - 3.9us (85˚C < TCASE < 95˚C)
- Asynchronous Reset pin supported
- Burst Length: 8 or BC4
- POD (Pseudo Open Drain) interface for data input/output
- Serial presence detect (SPD)
- All of products are Halogen-free
- All of Lead-Free products are compliant for RoHS

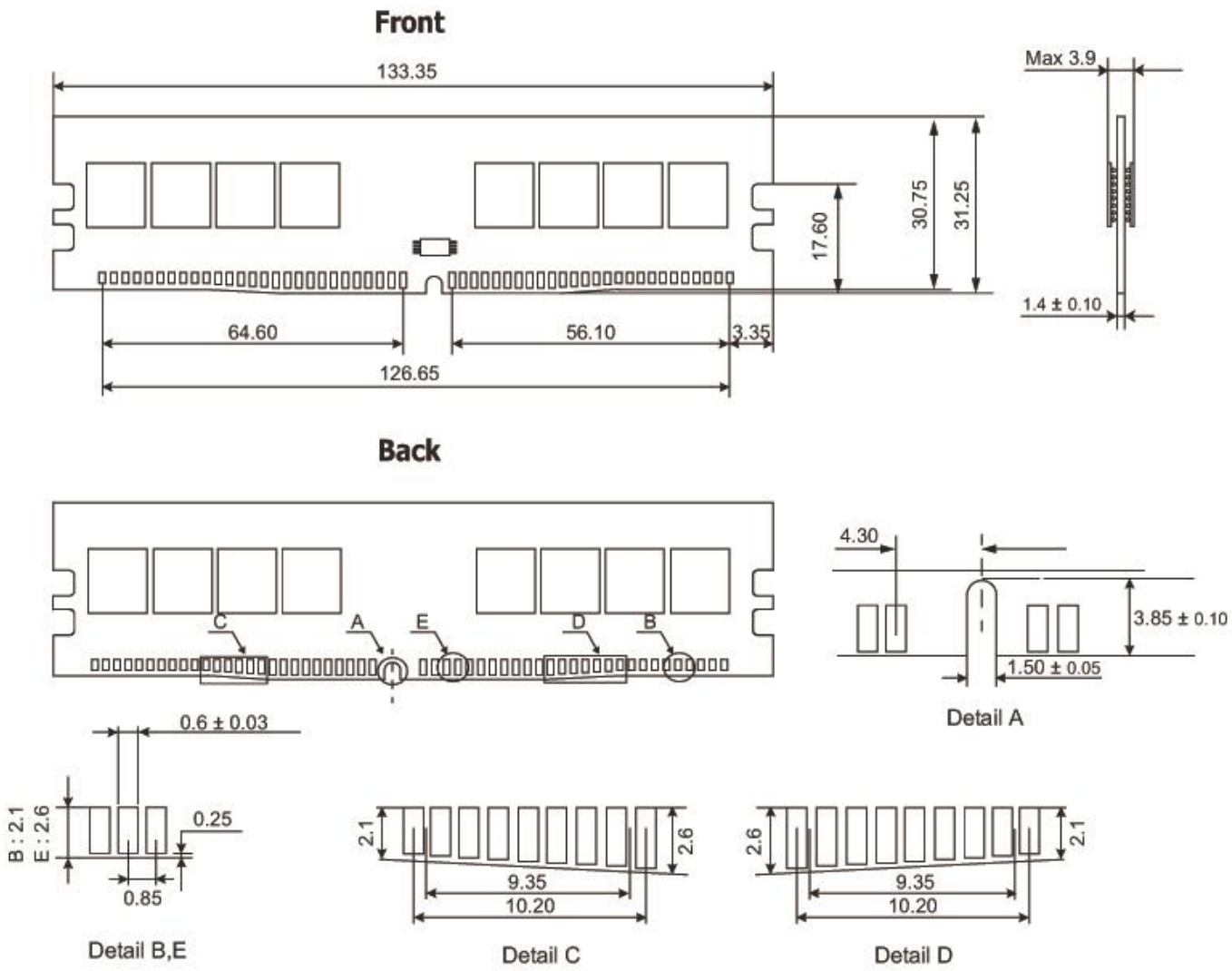
CIS-2ST385MOF001TW

Speed Grade

Frequency Grade	Data Transfer Rate	CAS Latency Support								CL-tRCD-tRP
		CL11	CL12	CL13	CL14	CL15	CL16	CL17	CL19	
DDR4-2666	PC4-21300	1600	1600	1866	1866	2133	2133	2400	2666	19-19-19

Package Dimensions

Unit: mm



Tolerances : ± 0.15mm unless otherwise specified